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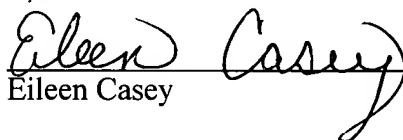
ATTORNEY DOCKET NO.: S1022/8800 <sup>2</sup>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Yvon GRIS, Germaine TROILLARD, and Jocelyne MOURIER  
Serial No: 09/988,233  
Filed: November 19, 2001  
For: METHOD OF DEPOSITION OF A SINGLE-CRYSTAL SILICON REGION  
  
Examiner: Unassigned  
Art Unit: 1765

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

The undersigned hereby certifies that this document is being placed in the United States mail with first-class postage attached, addressed to Box Missing Parts, Commissioner for Patents, Washington, D.C. 20231 on December 28, 2001.

  
Eileen Casey

Box Missing Parts  
Commissioner For Patents  
Washington, D.C. 20231

Sir:

**PRELIMINARY AMENDMENT**

Prior to examination, please amend this application as follows:

IN THE CLAIMS

Please cancel claims 1-10 without prejudice or disclaimer.

Please add the following new claims.

11. A method comprising:

forming defects in a region of a substrate; and

depositing a silicon layer on the region at a temperature of less than 750 °C.

12. The method of claim 11, comprising depositing the silicon layer at a temperature prior to annealing the substrate.